

Low-K factor of SiO₂ layer on Si irradiated by YAG:Nd laser

Medvid, A.; Onufrijevs, Pavels; **Mellikov, Enn**; **Kropman, Daniel**; Muktepavela, F.; Bakradze, G. Journal of non-crystalline solids 2007 / p. 703-707 : ill <https://www.sciencedirect.com/science/article/pii/S0022309306014116>

Stress relaxation mechanism by strain in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; **Mellikov, Enn**; Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262

Understanding and control of stress at Si-SiO₂ interface

Kropman, Daniel; Seeman, Viktor; Medvids, Arturs; Onufrijevs, Pavels; Vitusevich, Svetlana; **Mikli, Valdek** Key engineering materials 2020 / p. 291–296 <https://doi.org/10.4028/www.scientific.net/KEM.850.291> [Journal metrics at Scopus](#) [Article at Scopus](#)